



Session Title	[MoC2] Graphene I
Date / Time	July 2 (Mon.), 2018 / 13:30-15:30
Room	Room C (#107)
Session Chair	TBA

MoC2-I1 (Invited)

13:30-13:55

Valley-Symmetric Carrier Guiding in Ballistic Graphene

Hu-Jong Lee
POSTECH, Korea

MoC2-I2 (Invited)

13:55-14:20

Experimentally Tuning Graphene's Pseudospin Polarization and Valley Splitting

Markus Morgenstern
RWTH Aachen Univ., Germany

MoC2-I3 (Invited)

14:20-14:45

Plasmons and Sensing in Graphene Devices

Mikael Fogelström
Chalmers Univ. of Tech., Sweden

MoC2-I4 (Invited)

14:45-15:10

Graphene at The Charge Neutrality Point: Sensing at Terahertz Frequency Domain

Hans He¹, Samuel Lara-Avila¹, Kyung Ho Kim¹, Yung Woo Park², Rositsa Yakimova², Andrey Danilov¹, Dmitry Golubev³, Serguei Cherednichenko¹, and Sergey Kubatkin¹
¹*Chalmers Univ. of Tech., Sweden*, ²*Seoul Nat'l Univ., Korea*, ³*Low Temperature Lab., Aalto Univ., Finland*

MoC2-O5

15:10-15:25

Magnetic Field-Induced Metal-Insulator Transition of Graphene at A Filling Factor $\nu=0$

Sung Ju Hong, Christopher Belke, Johannes Rode, Benedikt Brechtken, and Rolf Haug
Leibniz Univ., Germany